



Schottky Barrier Diode

Features

1. Very low switching time
2. High reliability
3. Low leakage current
4. low forward voltage drop
5. Low capacitance



Applications

Diode for low currents with a low supply voltage

Small battery charger

HF-Detector

Protection circuit

DC/DC converter for notebooks

Protection circuit

Absolute Maximum Ratings

$T_j=25^{\circ}\text{C}$

Parameter	Test Conditions	Type	Symbol	Value	Unit
Reverse voltage		BAT81S	V_{RRM}	40	V
		BAT82S	V_{RRM}	50	V
		BAT83S	V_{RRM}	60	V
Repetitive peak forward current			I_{FRM}	150	mA
Peak forward surge current	$t_p=1\text{ s}$		I_{FSM}	500	mA
Forward current			I_F	30	mA
Junction temperature			T_j	125	$^{\circ}\text{C}$
Storage temperature range			T_{stg}	-65~+150	$^{\circ}\text{C}$

Stresses exceeding maximum ratings may damage the device. Maximum ratings are stress ratings only. Functional operation above the recommended operating conditions is not implied. Extended exposure to stresses above the recommended operating conditions may affect device reliability.

Excel Semiconductor

**Electrical Characteristics** $T_j=25^{\circ}\text{C}$

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=0.1\text{mA}$		V_F			0.33	V
	$I_F=1\text{mA}$		V_F			0.41	V
	$I_F=15\text{mA}$		V_F			1	V
Reverse current	$V_R=40\text{V}$	BAT81S	I_R			0.2	μA
	$V_R=50\text{V}$	BAT82S	I_R			0.2	μA
	$V_R=60\text{V}$	BAT83S	I_R			0.2	μA
Diode capacitance	$V_R=1\text{V}, f=1\text{MHz}$		C_D			1.6	pF



Characteristics ($T_j=25^\circ\text{C}$ unless otherwise specified)

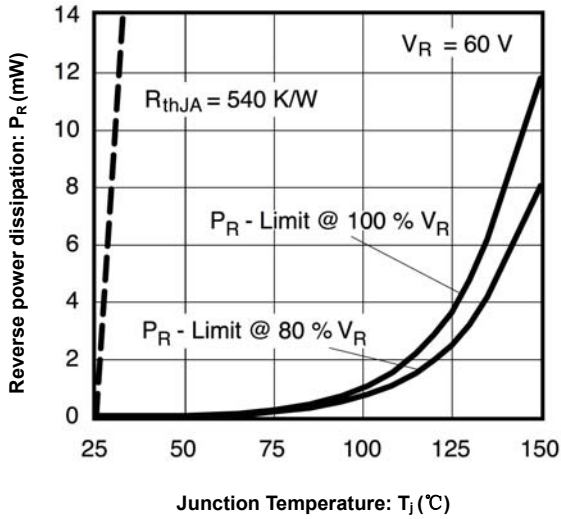


Figure 1. Max. reverse power dissipation vs. junction temperature

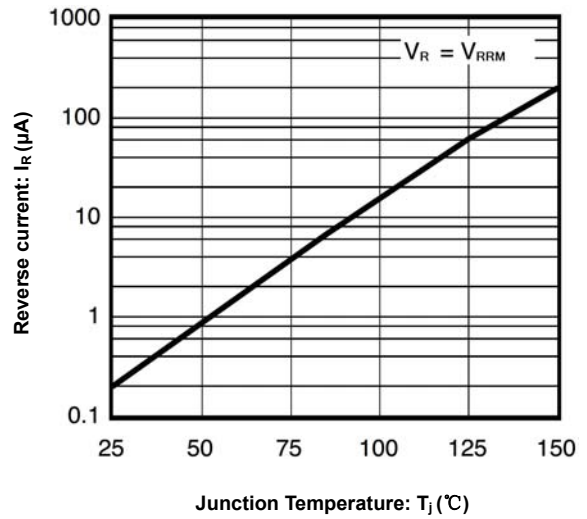


Figure 2. Reverse current vs. junction temperature

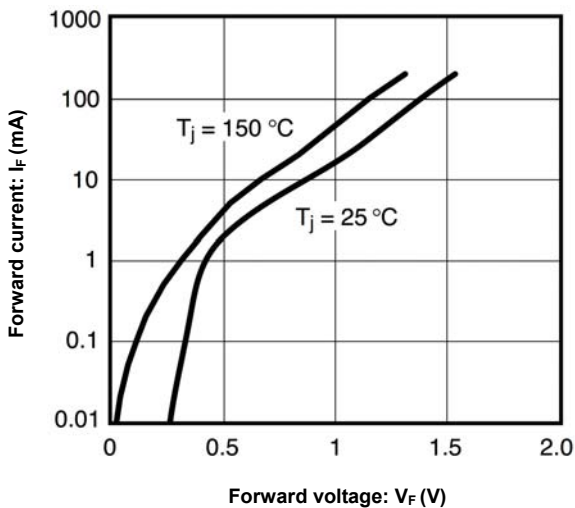


Figure 3. Forward current vs. forward voltage

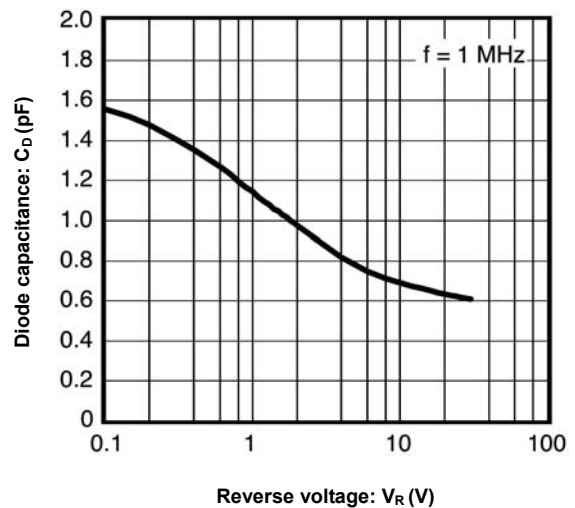
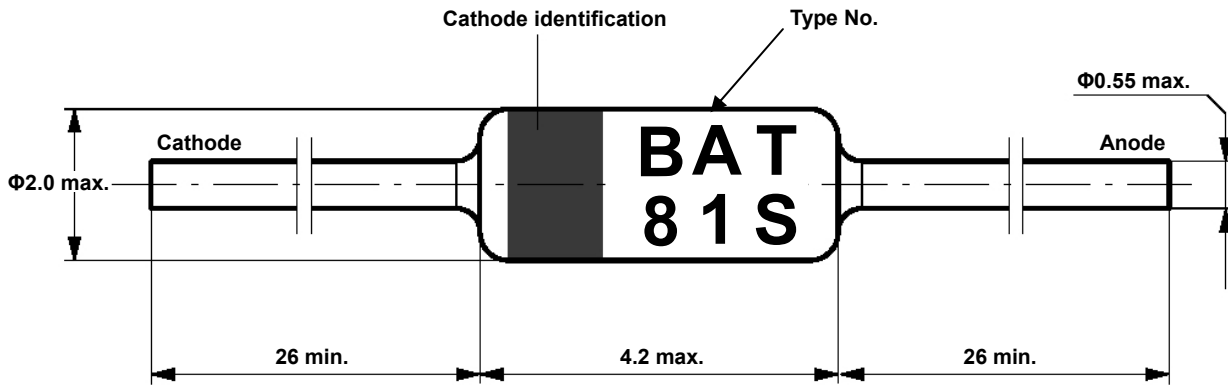


Figure 4. Diode capacitance vs. reverse voltage



Dimensions in mm



Standard Glass Case
JEDEC DO-35

Marking

